

# MC74HCT273A

## Octal D Flip-Flop with Common Clock and Reset with LSTTL-Compatible Inputs

### High-Performance Silicon-Gate CMOS

The MC74HCT273A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs.

The HCT273A is identical in pinout to the LS273.

This device consists of eight D flip-flops with common Clock and Reset inputs. Each flip-flop is loaded with a low-to-high transition of the Clock input. Reset is asynchronous and active low.

#### Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 V to 5.5 V
- Low Input Current: 1.0  $\mu$ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 284 FETs or 71 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

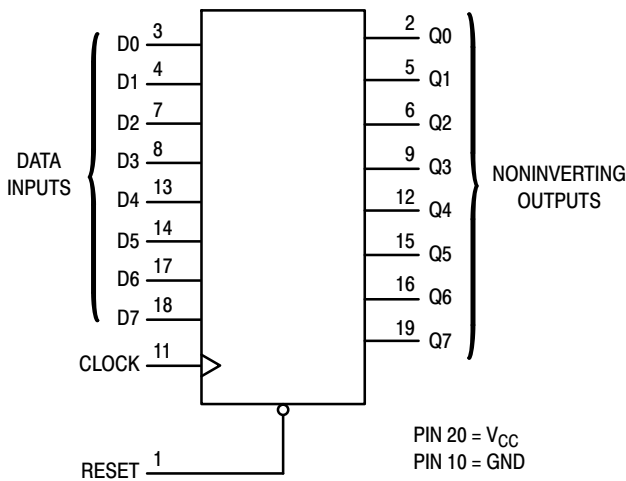
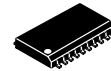


Figure 1. Logic Diagram

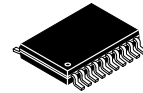


ON Semiconductor®

<http://onsemi.com>



SOIC-20W  
DW SUFFIX  
CASE 751D

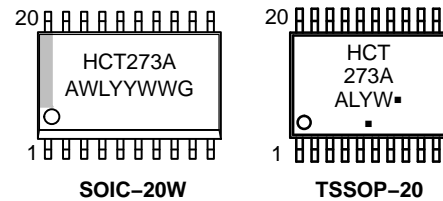


TSSOP-20  
DT SUFFIX  
CASE 948E

#### PIN ASSIGNMENT

RESET	1	20	V <sub>CC</sub>
Q0	2	19	Q7
D0	3	18	D7
D1	4	17	D6
Q1	5	16	Q6
Q2	6	15	Q5
D2	7	14	D5
D3	8	13	D4
Q3	9	12	Q4
GND	10	11	CLOCK

#### MARKING DIAGRAMS



A = Assembly Location  
 WL, L = Wafer Lot  
 YY, Y = Year  
 WW, W = Work Week  
 G or ■ = Pb-Free Package  
 (Note: Microdot may be in either location)

#### FUNCTION TABLE

Inputs			Output
Reset	Clock	D	Q
L	X	X	L
H	↗	H	H
H	↘	L	L
H	L	X	No Change
H	↔	X	No Change

X = Don't Care  
 Z = High Impedance

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

# MC74HCT273A

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
$V_{in}$	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
$V_{out}$	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
$I_{in}$	DC Input Current, per Pin	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 50$	mA
$P_D$	Power Dissipation in Still Air SOIC Package†	500	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
$V_{in}, V_{out}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	$V_{CC}$	V
$T_A$	Operating Temperature, All Package Types	-55	+125	°C
$t_r, t_f$	Input Rise and Fall Time (Figure 1)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	$V_{CC}$ V	Guaranteed Limit			Unit
				$\geq -55$ to 25°C	$\leq 85$ °C	$\leq 125$ °C	
$V_{IH}$	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5	2.0	2.0	2.0	V
			5.5	2.0	2.0	2.0	
$V_{IL}$	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5	0.8	0.8	0.8	V
			5.5	0.8	0.8	0.8	
$V_{OH}$	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5	4.4	4.4	4.4	V
			5.5	5.4	5.4	5.4	
$V_{OL}$	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	V
			5.5	0.1	0.1	0.1	
$I_{in}$	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or } GND$	4.5	0.1	0.1	0.1	μA
			5.5	0.26	0.33	0.4	
$I_{CC}$	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \mu\text{A}$	4.5	$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	μA
			5.5	4.0	40	160	
$\Delta I_{CC}$	Additional Quiescent Supply Current	$V_{in} = 2.4 \text{ V, Any One Input}$ $V_{in} = V_{CC} \text{ or } GND, \text{ Other Inputs}$ $I_{out} = 0 \mu\text{A}$	5.5	$\geq -55$ °C	25°C to 125°C		mA
				2.9	2.4		

# MC74HCT273A

## AC ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5.0\text{ V} \pm 10\%$ , $C_L = 50\text{ pF}$ , Input $t_r = t_f = 6.0\text{ ns}$ )

Symbol	Parameter	Fig.	Guaranteed Limit			Unit
			-55 to 25°C	≤ 85°C	≤ 125°C	
$f_{max}$	Maximum Clock Frequency (50% Duty Cycle)	2, 5	30	24	20	MHz
$t_{PLH}$ , $t_{PHL}$	Maximum Propagation Delay, Clock to Q	2, 5	25	28	35	ns
$t_{PHL}$	Maximum Propagation Delay, Reset to Q		25	28	35	ns
$t_{TLH}$ , $t_{THL}$	Maximum Output Transition Time, Any Output	2, 5	18	20	22	ns
$C_{PD}$	Power Dissipation Capacitance (Per Gate)*	Typical @ 25°C, $V_{CC} = 5.0\text{ V}$			pF	
		30				

\* Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

## TIMING REQUIREMENTS ( $V_{CC} = 5.0\text{ V} \pm 10\%$ , $C_L = 50\text{ pF}$ , Input $t_r = t_f = 6.0\text{ ns}$ )

Symbol	Parameter	Fig.	Guaranteed Limit						Unit
			-55 to 25°C		≤ 85°C		≤ 125°C		
			Min	Max	Min	Max	Min	Max	
$t_{su}$	Minimum Setup Time, Data to Clock		10		12		15		ns
$t_h$	Minimum Hold Time, Clock to Data		3.0		3.0		3.0		ns
$t_{rec}$	Minimum Recovery Time, Set or Reset Inactive to Clock		5.0		5.0		5.0		ns
$t_w$	Minimum Pulse Width, Clock	2	12		15		18		ns
$t_w$	Minimum Pulse Width, Set or Reset		12		15		18		ns
$t_r, t_f$	Maximum Input Rise and Fall Times	2		500		500		500	ns

## SWITCHING WAVEFORMS

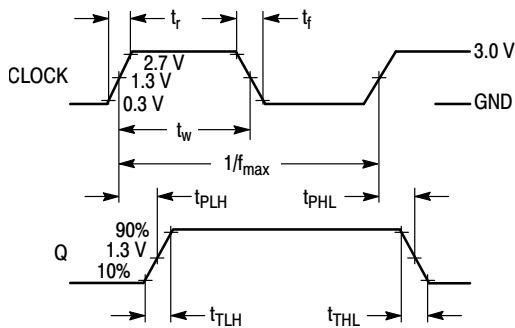


Figure 2.

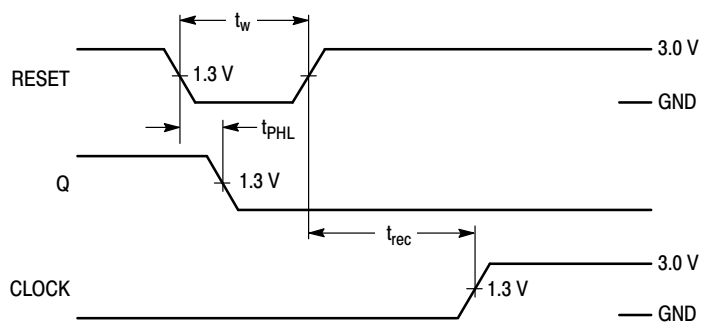


Figure 3.

# MC74HCT273A

## SWITCHING WAVEFORMS

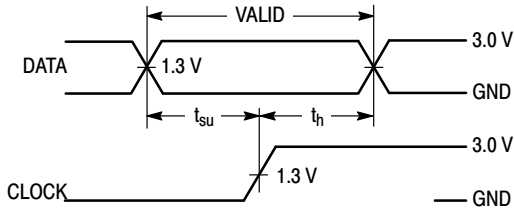
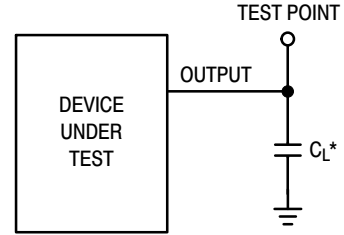


Figure 4.



\*Includes all probe and jig capacitance

Figure 5. Test Circuit

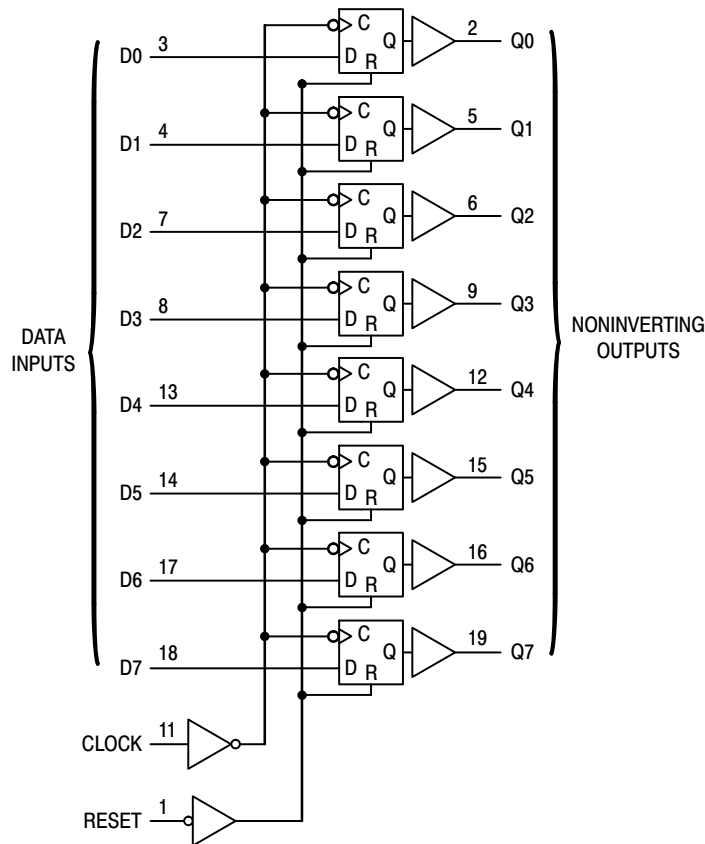


Figure 6. Expanded Logic Diagram

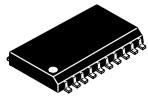
### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74HCT273ADWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74HCT273ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74HCT273ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

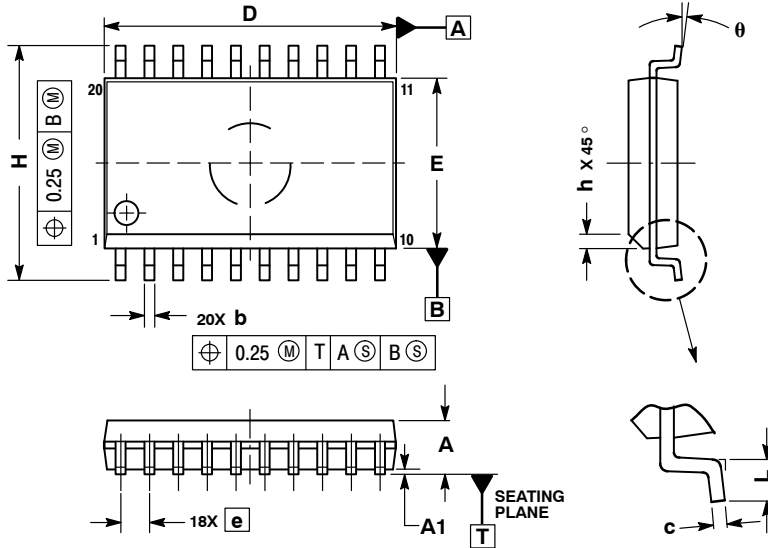
ON Semiconductor®



SCALE 1:1

SOIC-20 WB  
CASE 751D-05  
ISSUE H

DATE 22 APR 2015

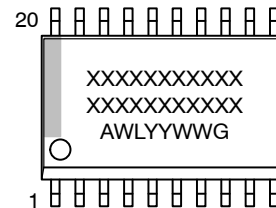


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

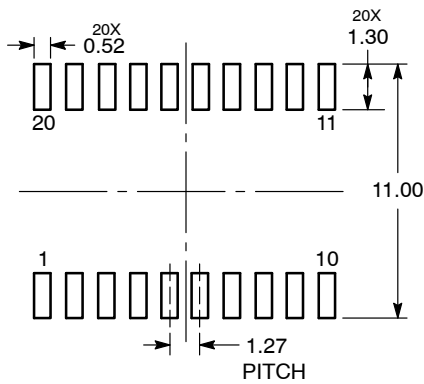
DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

### RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-20 WB	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-20 WB  
CASE 948E  
ISSUE D

DATE 17 FEB 2016

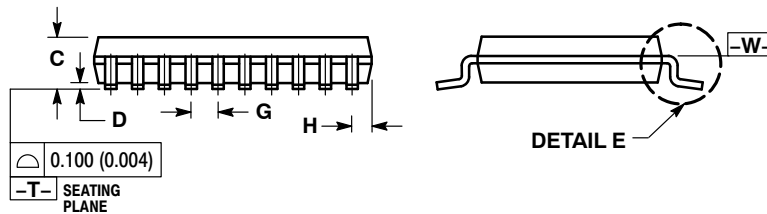
SCALE 2:1



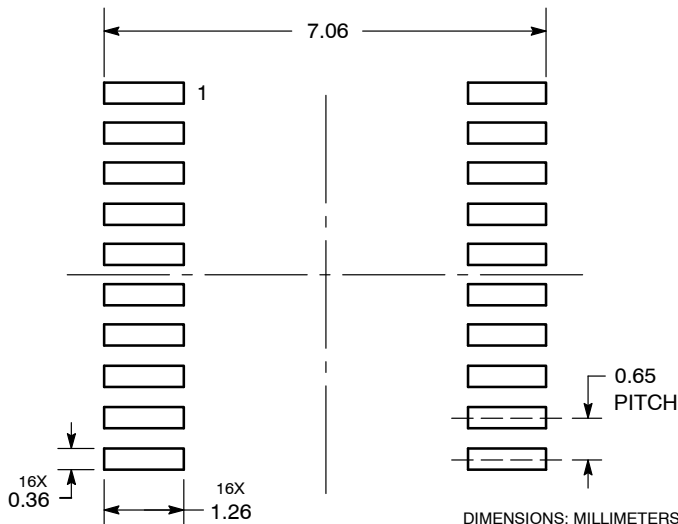
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

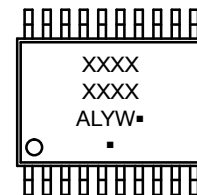
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP-20 WB	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.